

METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

ABSTRACT

5 A first heat treatment for crystallization is implemented after introducing nickel to an amorphous silicon film 103 disposed on a quartz substrate 101. A crystal silicon film 105 is obtained by this heat treatment. Then, an oxide film 106 is formed by wet oxidation. At this time, the nickel element is gettered to the oxide film 106 by an action of fluorite. Then, the oxide film 106 is removed. Thereby, a crystal silicon film 107 having low concentration of the metal element and a high crystallinity can be obtained.

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